

ABSTRACT OF THE DISCLOSURE

A source electrode, a gate electrode, and a drain electrode formed on a front face active region of a semiconductor substrate in a shape of teeth of a comb are covered with an insulating film such as polyimide etc., as well as all of the upper surface and the side surfaces of the insulating film are covered with a metal protective film. Via hole receiving pads connected to the source electrode, the gate electrode, and the drain electrode are respectively connected to bonding pads on a reverse face of the semiconductor substrate through via holes.